

IRF7751GTR-VB Datasheet

Dual P-Channel 30-V (D-S) MOSFET

PRODUCT SUMMARY			
V _{DS} (V)	$R_{DS(on)}(\Omega)$	I _D (A)	
- 30	0.036 at V _{GS} = - 10 V	- 5.2	
	0.055 at V _{GS} = - 4.5 V	- 4.2	

FEATURES

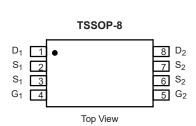
- · Halogen-free
- Trench Power MOSFETs

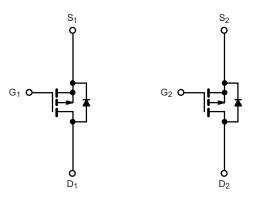


RoHS COMPLIANT

APPLICATIONS

- · Load Switch
- · Battery Switch





P-Channel MOSFET

P-Channel MOSFET

ABSOLUTE MAXIMUM RATINGS T _A = 25 °C, unless otherwise noted					
Parameter		Symbol	10 s	Steady State	Unit
Drain-Source Voltage		V _{DS}	- 30		V
Gate-Source Voltage		V_{GS}	± 20		V
Continuous Drain Current (T _J = 150 °C) ^a	T _A = 25 °C	I _D	- 5.2	- 4.1	
	T _A = 70 °C		- 4.2	- 3.6	٨
Pulsed Drain Current (10 µs Pulse Width)		I _{DM}	- 30		Α
Continuous Source Current (Diode Conduction) ^a		I _S	- 1.0	- 0.70	
M · D D · · · · · 3	T _A = 25 °C	В	1.14	0.83	W
Maximum Power Dissipation ^a	T _A = 70 °C	P_{D}	0.73	0.53	
Operating Junction and Storage Temperature Range		T _J , T _{stq}	- 55	to 150	°C

THERMAL RESISTANCE RATINGS					
Parameter		Symbol	Typical	Maximum	Unit
	t ≤ 10 s	R_{thJA}	86	110	
Maximum Junction-to-Ambient ^a	Steady State		124	150	°C/W
Maximum Junction-to-Foot	Steady State	R _{thJF}	52	65	

Notes:

a. Surface Mounted on 1" x 1" FR4 board.

服务热线:400-655-8788

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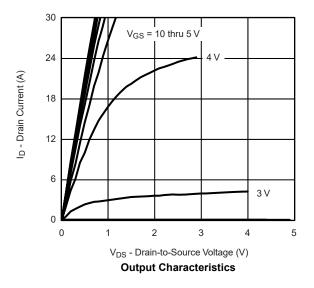
Parameter	Symbol	Test Conditions	Min.	Тур.	Max.	Unit
Static						
Gate Threshold Voltage	V _{GS(th)}	$V_{DS} = V_{GS}, I_{D} = -250 \mu A$	- 1.0		- 3.0	V
Gate-Body Leakage	I _{GSS}	V _{DS} = 0 V, V _{GS} = ± 20 V			± 100	nA
7 0 1 1/1 5 1 0 1		V _{DS} = - 30 V, V _{GS} = 0 V			- 1	μΑ
Zero Gate Voltage Drain Current	I _{DSS}	V _{DS} = - 30 V, V _{GS} = 0 V, T _J = 55 °C			- 10	
On-State Drain Current ^a	I _{D(on)}	V _{DS} ≥ - 5 V, V _{GS} = - 10 V	- 15			Α
5	Б	V _{GS} = - 10 V, I _D = - 4.7 A		0.036		0
Drain-Source On-State Resistance ^a	R _{DS(on)}	V _{GS} = - 4.5 V, I _D = - 3.8 A		0.055		Ω
Forward Transconductance ^a	9 _{fs}	V _{DS} = - 15 V, I _D = - 4.7 A		14		S
Diode Forward Voltage ^a	V_{SD}	I _S = - 1.0 A, V _{GS} = 0 V		- 0.74	- 1.1	V
Dynamic ^b				'		
Total Gate Charge	Q_g			13	20	
Gate-Source Charge	Q_{gs}	$V_{DS} = -15 \text{ V}, V_{GS} = -4.5 \text{ V}, I_{D} = -4.7 \text{ A}$		3		nC
Gate-Drain Charge	Q_{gd}			5.8		
Gate Resistance	R_g	f = 1.0 MHz		4.6		Ω
Turn-On Delay Time	t _{d(on)}			13	20	
Rise Time	t _r	V_{DD} = - 15 V, R_L = 15 Ω		14	22	
Turn-Off Delay Time	t _{d(off)}	$I_D\cong$ - 1 A, V_{GEN} = - 10 V, R_G = 6 Ω		52	80	ns
Fall Time	t _f			26	40	
Source-Drain Reverse Recovery Time	t _{rr}	I _F = - 1.0 A, dl/dt = 100 A/μs		40	60	

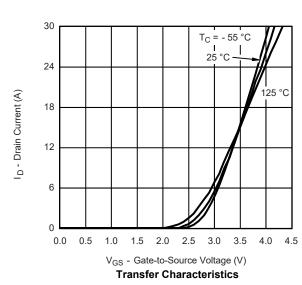
Notes:

- a. Pulse test; pulse width \leq 300 µs, duty cycle \leq 2 %.
- b. Guaranteed by design, not subject to production testing.

Stresses beyond those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated in the operational sections of the specifications is not implied. Exposure to absolute maximum rating conditions for extended periods may affect device reliability.

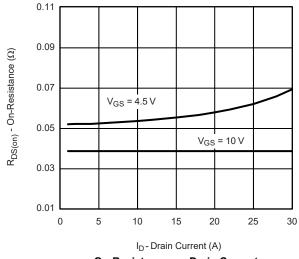
TYPICAL CHARACTERISTICS 25 °C, unless otherwise noted



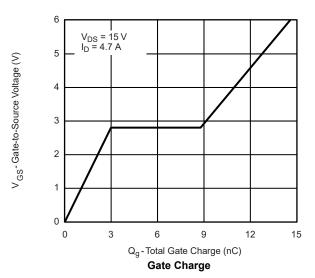




TYPICAL CHARACTERISTICS 25 °C, unless otherwise noted

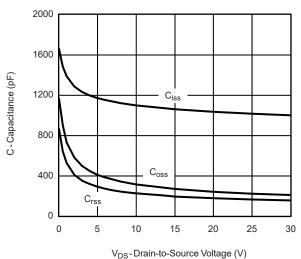


On-Resistance vs. Drain Current

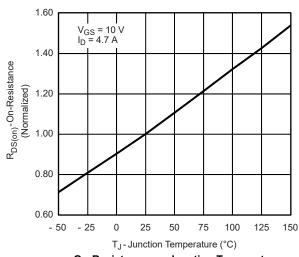


T_J = 150 °C

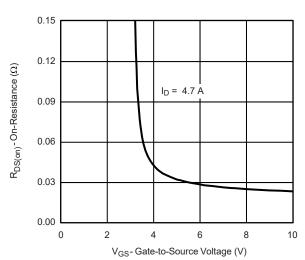
 $\label{eq:VSD-Source-to-Drain Voltage} V_{SD}\text{-}\,\text{Source-to-Drain Voltage} \ (\text{V})$ Source-Drain Diode Forward Voltage



Capacitance



On-Resistance vs. Junction Temperature



On-Resistance vs. Gate-to-Source Voltage

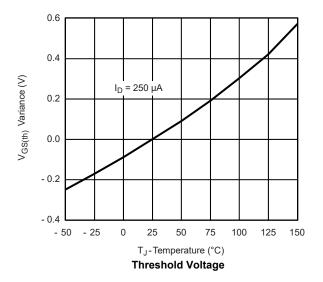
服务热线:400-655-8788

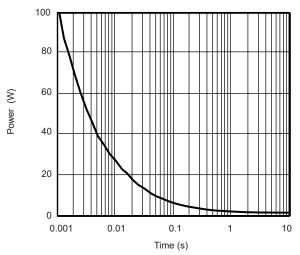
30

10

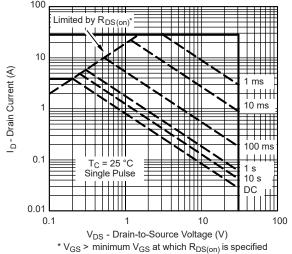


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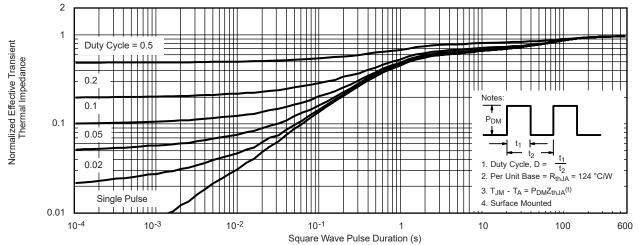




Single Pulse Power, Junction-to-Ambient



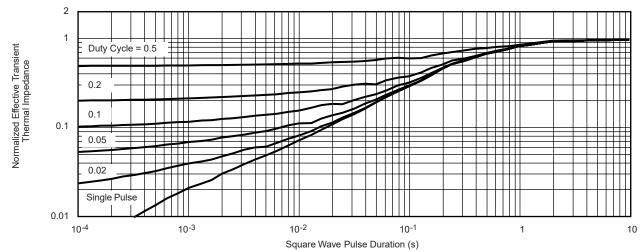
Safe Operating Area, Junction-to-Case



Normalized Thermal Transient Impedance, Junction-to-Ambient



TYPICAL CHARACTERISTICS 25 °C, unless otherwise noted

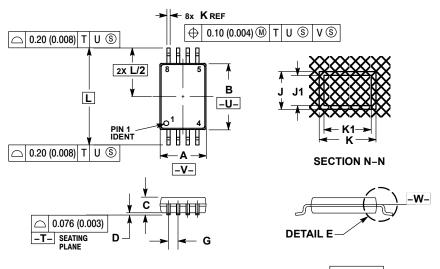


Normalized Thermal Transient Impedance, Junction-to-Foot



TSSOP-8





	MILLIN	IETERS	INCHES	
DIM	MIN	MAX	MIN	MAX
Α	2.90	3.10	0.114	0.122
В	4.30	4.50	0.169	0.177
С		1.10	-	0.043
D	0.05	0.15	0.002	0.006
F	0.50	0.70	0.020	0.028
G	0.65 BSC		0.026 BSC	
J	0.09	0.20	0.004	0.008
J1	0.09	0.16	0.004	0.006
K	0.19	0.30	0.007	0.012
K1	0.19	0.25	0.007	0.010
L	6.40 BSC		0.252	
M	0°	8°	0	8°

N —	0.25 (0.010)		
N F	M		
DETAIL E			



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